BT231-800D-L

4Q Triac

Rev.01 - 08 October 2026 Product data sheet

1. General description

Planar passivated very sensitive gate four quadrant triac in a TO92 plastic package intended for use in applications requiring direct interfacing to logic ICs and low power gate drivers.

2. Features and benefits

- High blocking voltage capability
- Very sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits

3. Applications

- Industrial process control
- General purpose low power motor control
- Home appliances
- Low power AC Fan controllers

4. Quick reference data

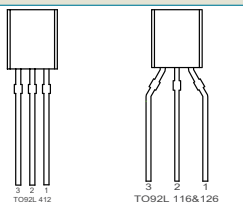
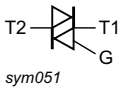
Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V_{DRM}	repetitive peak off-state voltage			800			V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 66$ °C; Fig. 1; Fig. 2; Fig. 3		1			A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5		11			A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms		12.1			A
T_j	operating junction temperature			-40 to 125			°C
Symbol	**Parameter**	**Conditions**	**Notes**	**Min**	**Typ**	**Max**	**Unit**
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12$ V; $I_T = 0.1$ A; T2+ G+; $T_j = 25$ °C; Fig. 7		-	-	5	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2+ G-; $T_j = 25$ °C; Fig. 7		-	-	3	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2- G-; $T_j = 25$ °C; Fig. 7		-	-	3	mA
		$V_D = 12$ V; $I_T = 0.1$ A; T2- G+; $T_j = 25$ °C; Fig. 7		-	-	10	mA

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	10	mA
V_T	on-state voltage	I_T = 1 A; T_j = 25 °C; Fig. 10		-	1.3	1.5	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		100	-	-	V/µs
dV_{com}/dt	rate of change of commutating voltage	V_D = 400 V; T_j = 125 °C; dI_{com}/dt = 0.5 A/ms; gate open circuit		0.5	-	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		
2	G	gate		
3	T1	main terminal 1		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT231-800D-L	TO92	BT231-800D-L,412	Bulk	1000	TO92L	10-May-2021
		BT231-800D-L,116	Reel	2000	TO92L	10-May-2021

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT231-800D-L	231D8L

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DRM}	repetitive peak off-state voltage			800	V
V_{RRM}	repetitive peak reverse voltage			800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{sp} \leq 66$ °C; Fig 1; Fig 2; Fig 3		1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig 4; Fig 5		11	A
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms		12.1	A
I^2t	I^2t for fusing	$t_p = 10$ ms; SIN		0.6	A^2s
dI_T/dt	rate of rise of on-state current	$I_G = 10$ mA		50	A/µs
I_{GM}	peak gate current			1	A
P_{GM}	peak gate power			2	W
$P_{G(AV)}$	average gate power	over any 20 ms period		0.1	W
T_{stg}	storage temperature			-40 to 150	°C
T_j	operating junction temperature			-40 to 125	°C

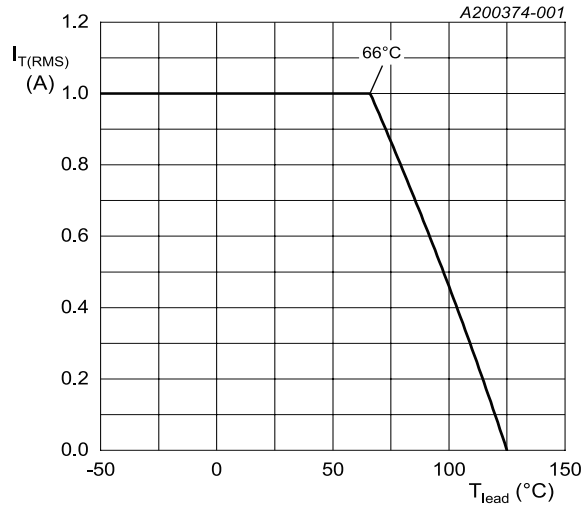
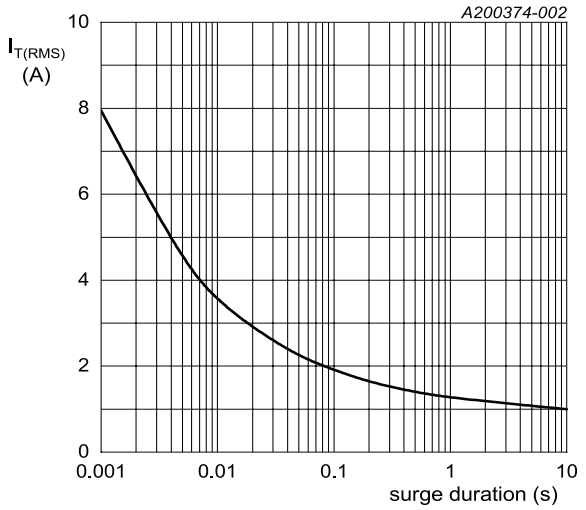


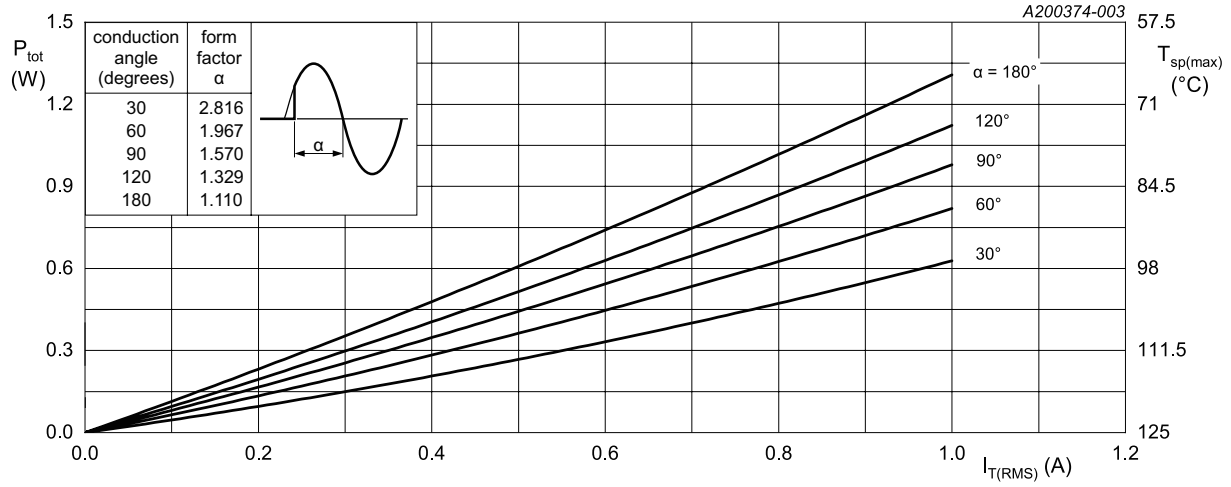
Fig. 1. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz; T_{lead} = 66 °C

Fig. 2. RMS on-state current as a function of surge duration; maximum values

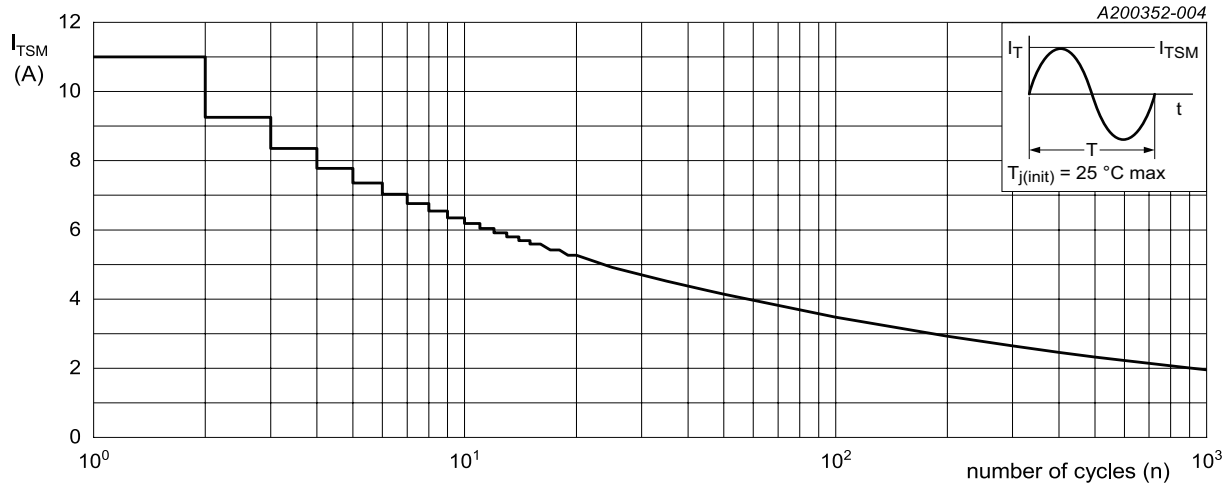
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α = conduction angle

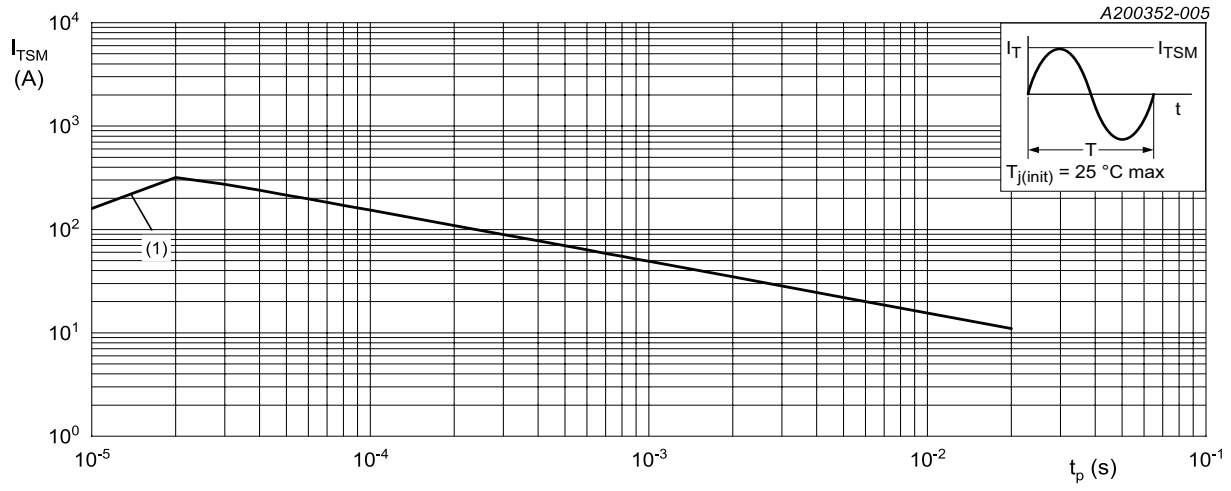
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



t_p ≤ 20 ms

(1) dI_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j\text{-}lead)}$	thermal resistance from junction to lead	Fig 6		-	-	45	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	in free air		-	150	-	K/W

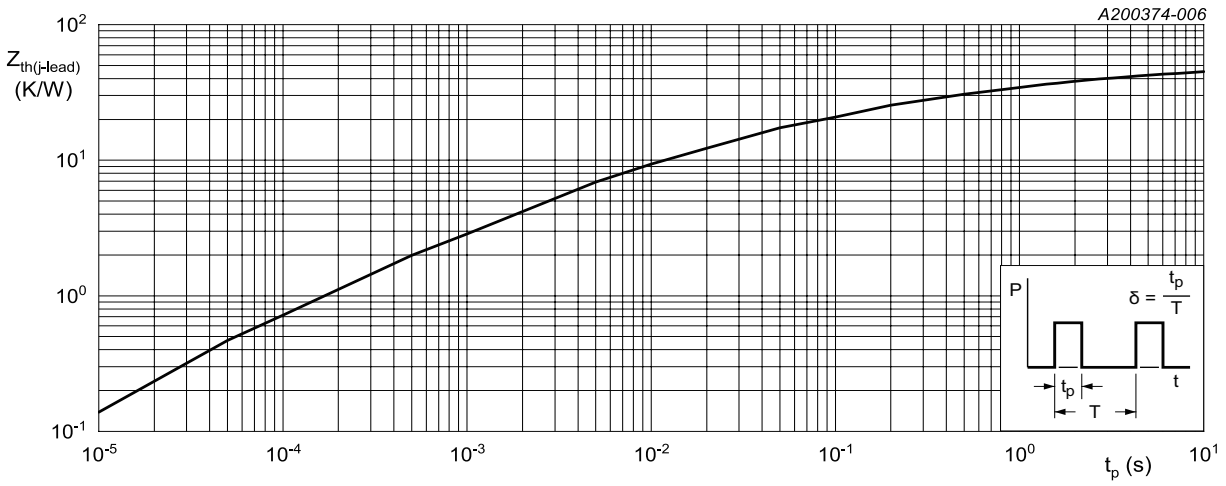


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		-	-	5	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		-	-	3	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		-	-	3	mA
		V_D = 12 V; I_T = 0.1 A; T2- G+; T_j = 25 °C; Fig. 7		-	-	10	mA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 8		-	-	10	mA
		V_D = 12 V; I_G = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 8		-	-	10	mA
		V_D = 12 V; I_G = 0.1 A; T2- G-; T_j = 25 °C; Fig. 8		-	-	10	mA
		V_D = 12 V; I_G = 0.1 A; T2- G+; T_j = 25 °C; Fig. 8		-	-	20	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	10	mA
V_T	on-state voltage	I_T = 1 A; T_j = 25 °C; Fig. 10		-	1.3	1.5	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 11		-	-	1	V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 °C		0.2	-	-	V
I_D	off-state current	V_D = 800 V; T_j = 25 °C		-	-	10	µA
		V_D = 800 V; T_j = 125 °C		-	-	0.5	mA
I_R	reverse current	V_R = 800 V; T_j = 25 °C		-	-	10	µA
		V_R = 800 V; T_j = 125 °C		-	-	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		100	-	-	V/µs
dV_{com}/dt	rate of change of commutating voltage	V_D = 400 V; T_j = 125 °C; dI_{com}/dt = 0.5 A/ms; gate open circuit		0.5	-	-	V/µs

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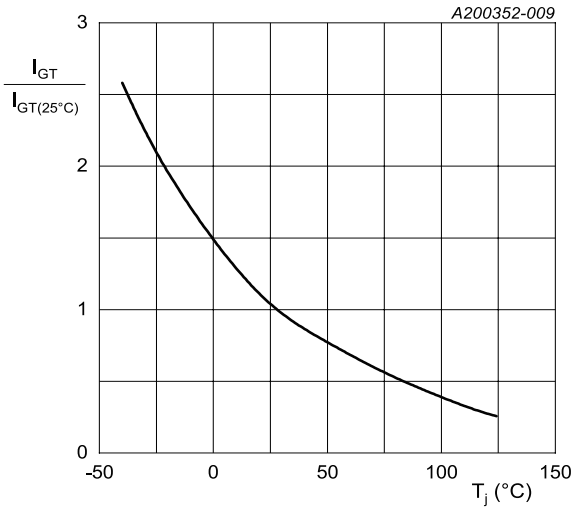


Fig. 7. Normalized gate trigger current as a function of junction temperature

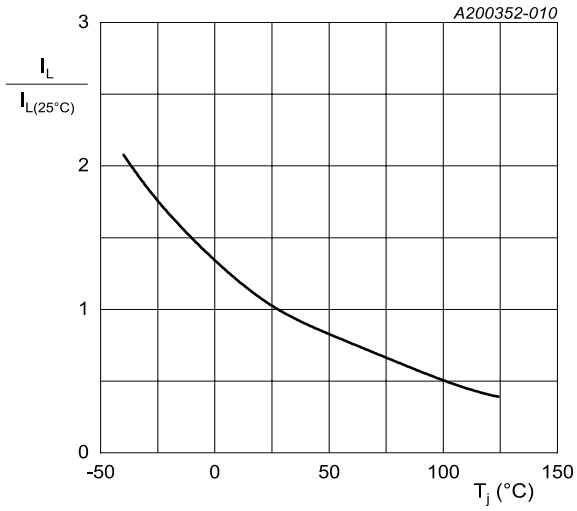


Fig. 8. Normalized latching current as a function of junction temperature

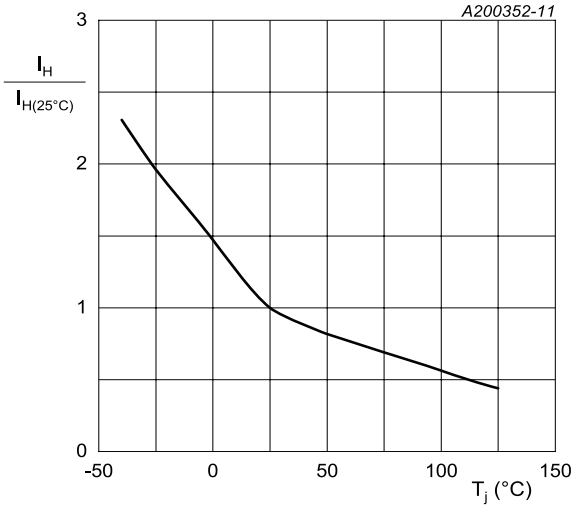
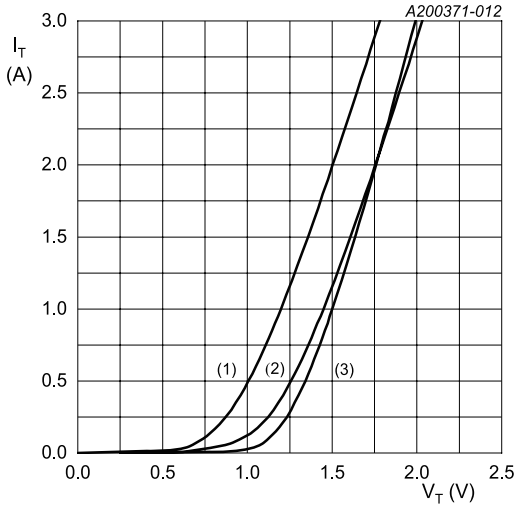


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 1.246 V; R_s = 0.1850 Ω
(1) T_j = 125 °C; typical values
(2) T_j = 125 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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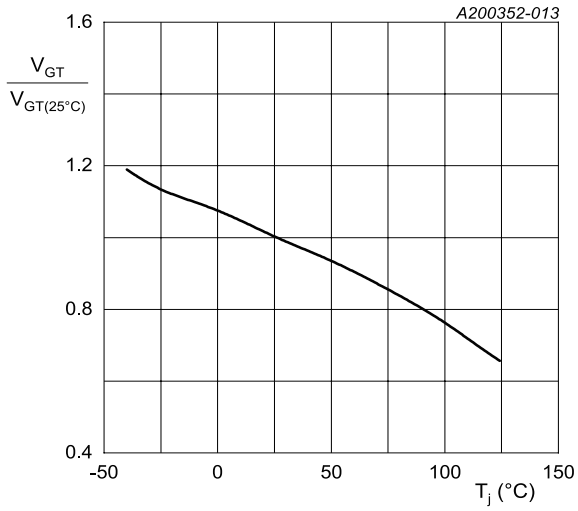


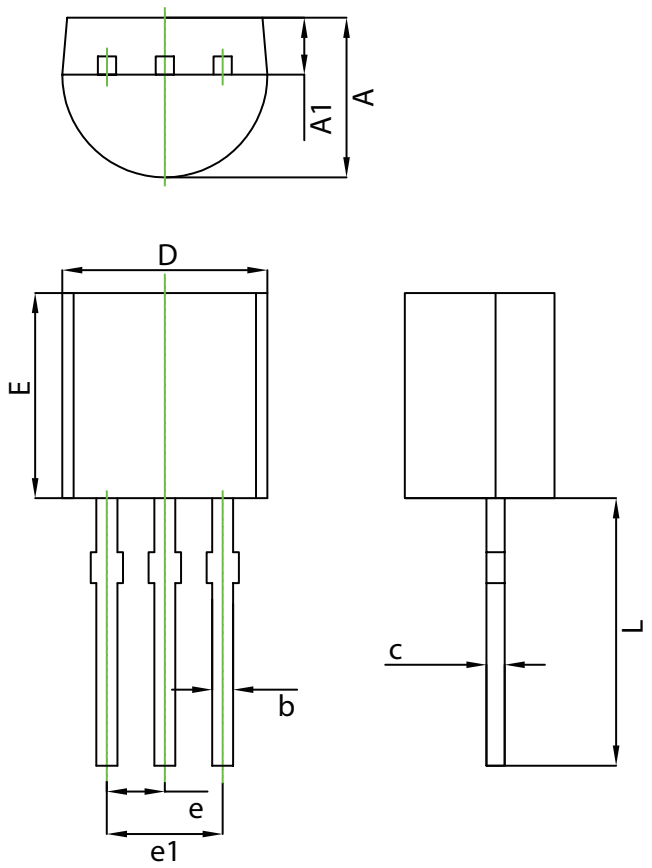
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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11. Package outline

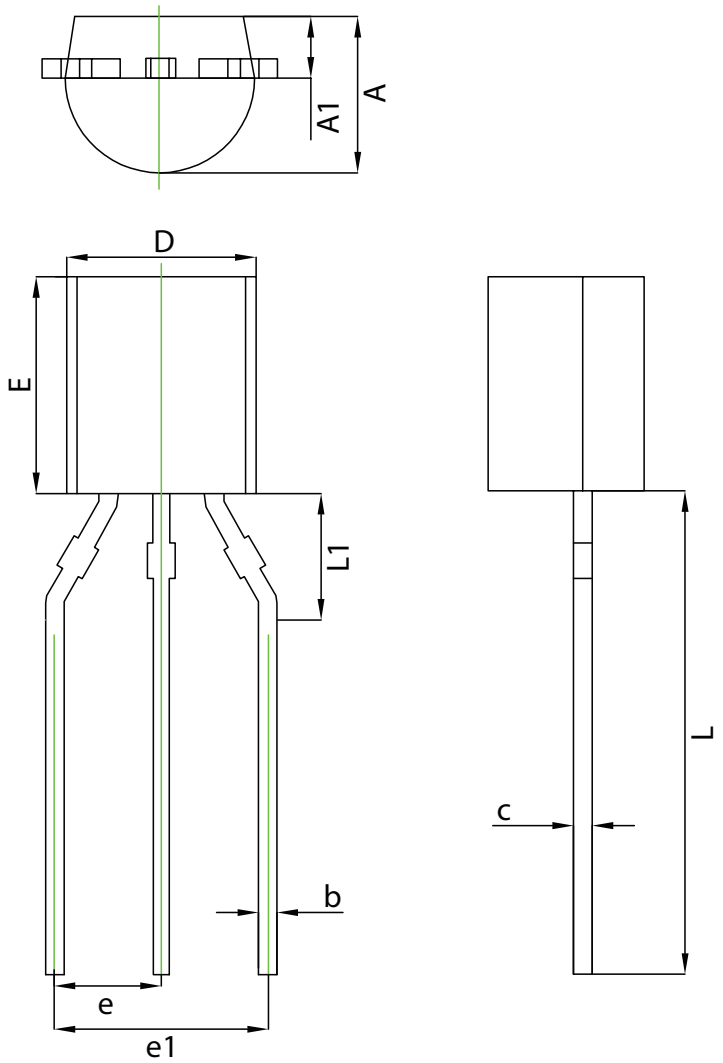
Plastic single-ended leaded(through hole) package; 3 leads TO92



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
E	4.300	4.700	0.169	0.185
e	1.270 TYP.		0.050 TYP.	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571

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TO92L 116&126



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
E	4.300	4.700	0.169	0.185
e	2.500BSC.		0.098BSC.	
e1	5.000BSC.		0.197BSC.	
L	13.300	13.700	0.524	0.539
L1	3.00TYP.		0.118TYP.	

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Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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